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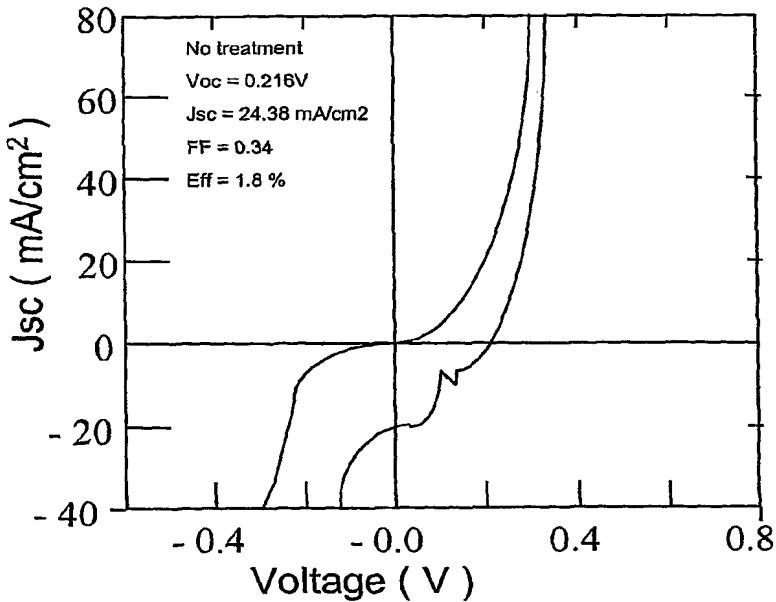
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(54) Title: ZNO/CU(INGA)SE₂ SOLAR CELLS PREPARED BY VAPOR PHASE ZN DOPING



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(57) **Abstract:** A process for making a thin film ZnO/Cu(InGa)Se₂ solar cell without depositing a buffer layer and by Zn doping from a vapor phase, comprising: depositing Cu(InGa)Se₂ layer on a metal back contact deposited on a glass substrate; heating the Cu(InGa)Se₂ layer on the metal back contact on the glass substrate to a temperature range between about 100 °C to about 250 °C; subjecting the heated layer of Cu(InGa)Se₂ to an evaporant species from a Zn compound; and sputter depositing ZnO on the Zn compound evaporant species treated layer of Cu(InGa)Se₂.